MBR3520 MBR3535 MBR3545, H, H1

SWITCHMODE POWER RECTIFIERS

PO BOX 20912 • PHOENIX, ARIZONA 85036

... using a platinum barrier metal in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free-wheeling diodes, and polarity-protection diodes.

- Guardring for dv/dt Stress Protection
- Guaranteed Reverse Surge Current/Avalanche
- 150°C Operating Junction Temperature

SCHOTTKY BARRIER RECTIFIERS

35 AMPERES 20 to 45 VOLTS



CASE 245 DO-4

MAXIMUM RATINGS

| Rating | Symbol | MBR3520 | MBR3535 | MBR3545, H, H1* | Unit |
|---|--------------------|---------|-----------|-----------------|-------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | VRRM VRWM VR | 20 | 35 | 45 | Volts |
| Peak Repetitive Forward Current (Rated Vp., Square Wave, 20 kHz) | FRM | | 70- | | Amps |
| Average Rectified Forward Current (Rated VR) | IF(AV) | - | 70 - | | Amps |
| Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 8 | IRRM | | 2.0 - | - | Amps |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | ^I FSM | 4 | 600 | | Amps |
| Operating Junction Temperature | TJ | 4 | -65 to + | 50 | °C |
| Storage Temperature | T _{stg} | - | -65 to +1 | 75 | °C |
| Voltage Rate of Change (Rated V _R) | dv/dt | 4 | 1000 | | V/µs |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Тур | Max | Unit |
|--------------------------------------|--------|-----|-----|------|
| Thermal Resistance, Junction-to-Case | ReJC | 1.3 | 1.5 | °C/W |

ELECTRICAL CHARACTERISTICS PER DIODE

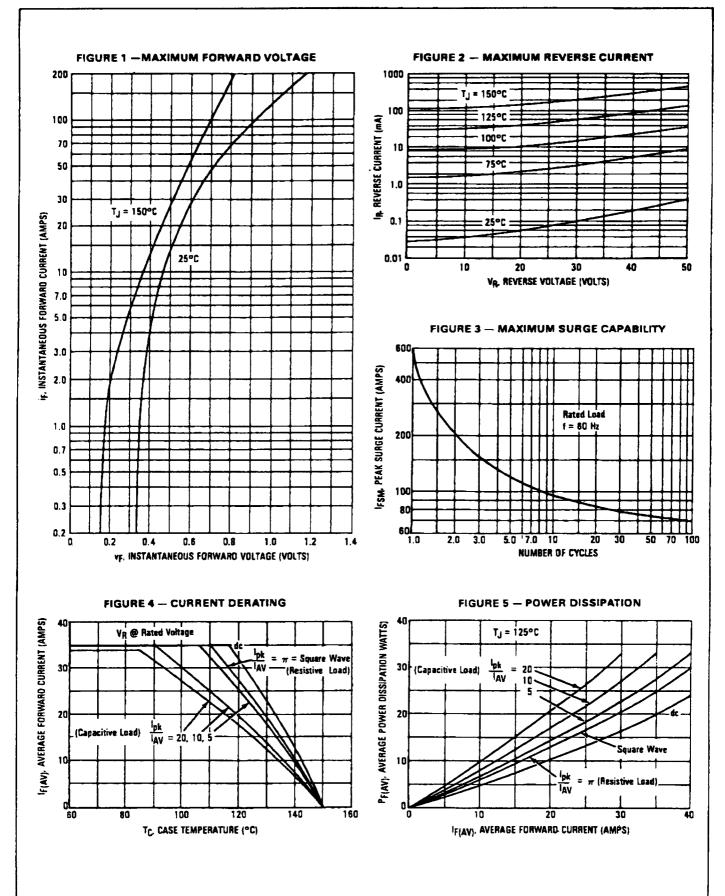
| Characteristic | Symbol | Тур | Max | Unit |
|---|----------------|------|------|-------|
| Instantaneous Forward Voltage (1) | VF | | | Volts |
| (ip = 35 Amp, T _C = 125°C) | , i | 0.49 | 0.55 | |
| (ip = 35 Amp, T _C = 25°C) | | 0.55 | 0.63 | |
| (i _F = 70 Amp, T _C = 125°C) | Į. | 0.60 | 0.69 | |
| Instantaneous Reverse Current (1) | İR | | İ | mA |
| (Rated Voltage, T _C = 125°C) | " } | 60 | 100 | |
| (Rated Voltage, T _C = 25°C) | | 0.1 | 0.3 | |
| Capacitance ($V_R = 1.0 \text{ Vdc}$, 100 kHz>f>1.0 MHz, $T_C = 25^{\circ}\text{C}$) | C _t | 3000 | 3700 | pF |

^{*}H and H1 devices include extra testing. See Figure 10.

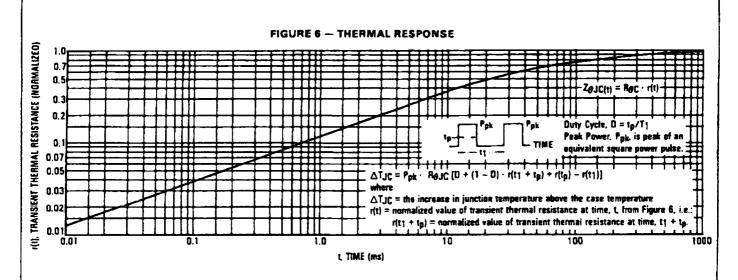
MOTOROLA INC., 1981

DS6104 R1

⁽¹⁾ Pulse Test: Pulse Width = 300 μ s. Duty Cycle = 2.0%



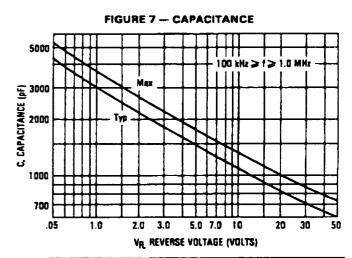


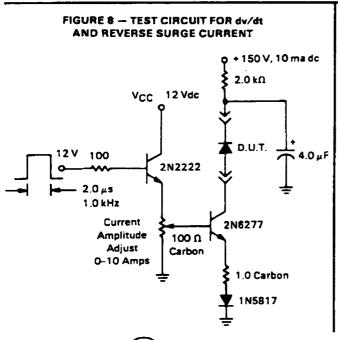


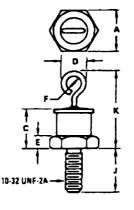
HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 7.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.







| | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| DIM | MIN | MAX | MIN | MAX |
| A | 10.77 | 11.10 | 0.424 | 0.437 |
| C | - | 10.29 | 1 | 0.405 |
| 0 | | 8.35 | | 0.250 |
| E | 1.51 | 4.45 | 0.075 | 0.175 |
| F | 1.52 | _ | 0.060 | - |
| | 10.72 | 11.51 | 0.422 | 0.453 |
| K | - | 20.32 | - | 0.800 |

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corresion resistant and terminal lead is readily selderable.

POLARITY: Cathode-to-Case

MOUNTING POSITION: Any

STUD TORQUE: 25 m.-tb Max

SOLDER HEAT: The exceptent heat transfer properly of the heavy duty copper anode terminal which transmits heat away from the die requires that caution be used when attaching wires. Mosorola suggests a heat sink be clamped between the eyelet and the body during any soldering operation.

CASE 245
(DO-4)
Polarity: Cathode to Case



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